Abstracts

Characterization of W-band MMIC power amplifier using on-wafer pulsed power test

D.C. Yang, J.M. Yang, H. Wiang and P. Huang. "Characterization of W-band MMIC power amplifier using on-wafer pulsed power test." 1998 MTT-S International Microwave Symposium Digest 98.3 (1998 Vol. III [MWSYM]): 1483-1486.

A facile technique based on pulsed power test has been developed to characterize W-band MMIC power amplifiers and optimize their gain and PAE (power added efficiency) on-wafer. By suppressing thermal effects usually associated with conventional on-wafer tests, the pulsed power technique makes it possible to not only establish device binning criteria but also eliminate in-module bias tuning. It thus provides significant cost savings in volume production environments.

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